



# CNY171M, CNY172M, CNY173M, CNY174M, CNY17F1M, CNY17F2M, CNY17F3M, CNY17F4M, MOC8106M, MOC8107M Phototransistor Optocouplers

## Features

- UL recognized (File # E90700, Vol. 2)
- VDE recognized
  - Add option V (e.g., CNY17F2VM)
  - File #102497
- Current transfer ratio in select groups
- High  $BV_{CEO}$ : 70V minimum (CNY17XM, CNY17FXM, MOC810XM)
- Closely matched current transfer ratio (CTR) minimizes unit-to-unit variation.
- Very low coupled capacitance along with no chip to pin 6 base connection for minimum noise susceptibility (CNY17FXM, MOC810XM)

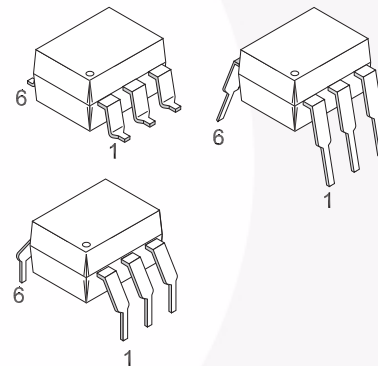
## Applications

- Power supply regulators
- Digital logic inputs
- Microprocessor inputs
- Appliance sensor systems
- Industrial controls

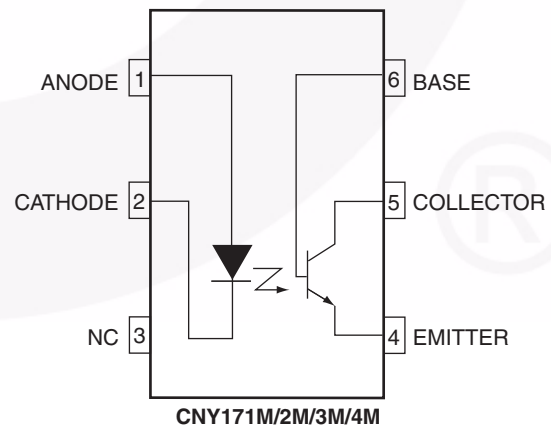
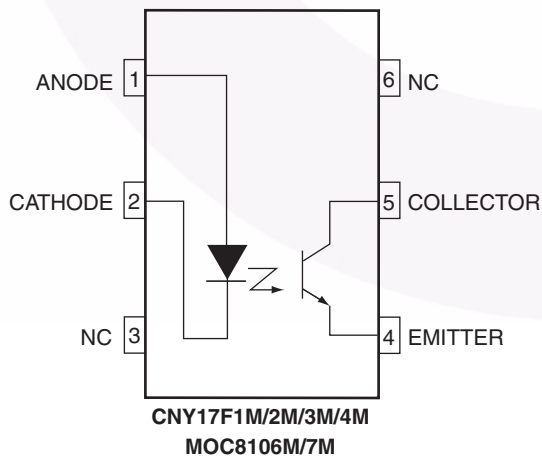
## Description

The CNY17XM, CNY17FXM and MOC810XM devices consist of a Gallium Arsenide IRED coupled with an NPN phototransistor in a dual in-line package.

## Package Outlines



## Schematics



## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Value	Units
<b>TOTAL DEVICE</b>			
T <sub>STG</sub>	Storage Temperature	-40 to +150	°C
T <sub>OPR</sub>	Operating Temperature	-40 to +100	°C
T <sub>SOL</sub>	Lead Solder Temperature	260 for 10 sec	°C
P <sub>D</sub>	Total Device Power Dissipation @ 25°C (LED plus detector) Derate Linearly From 25°C	250	mW
		2.94	mW/°C
<b>EMITTER</b>			
I <sub>F</sub>	Continuous Forward Current	60	mA
V <sub>R</sub>	Reverse Voltage	6	V
I <sub>F</sub> (pk)	Forward Current – Peak (1µs pulse, 300pps)	1.5	A
P <sub>D</sub>	LED Power Dissipation 25°C Ambient Derate Linearly From 25°C	120	mW
		1.41	mW/°C
<b>DETECTOR</b>			
I <sub>C</sub>	Continuous Collector Current	50	mA
V <sub>CEO</sub>	Collector-Emitter Voltage	70	V
V <sub>ECO</sub>	Emitter Collector Voltage	7	V
P <sub>D</sub>	Detector Power Dissipation @ 25°C Derate Linearly from 25°C	150	mW
		1.76	mW/°C

## Electrical Characteristics (T<sub>A</sub> = 25°C Unless otherwise specified.)<sup>(1)</sup>

### Individual Component Characteristics

Symbol	Parameters	Test Conditions	Device	Min.	Typ.	Max.	Units
<b>EMITTER</b>							
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 60mA	CNY17XM, CNY17FXM	1.0	1.35	1.65	V
		I <sub>F</sub> = 10mA	MOC810XM	1.0	1.15	1.50	
C <sub>J</sub>	Capacitance	V <sub>F</sub> = 0 V, f = 1.0MHz	All		18		pF
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 6V	All		0.001	10	μA
<b>DETECTOR</b>							
BV <sub>CEO</sub>	Breakdown Voltage Collector to Emitter	I <sub>C</sub> = 1.0mA, I <sub>F</sub> = 0	All	70	100		V
BV <sub>CBO</sub>	Collector to Base	I <sub>C</sub> = 10μA, I <sub>F</sub> = 0	CNY171M/2M/3M/4M	70	120		
BV <sub>ECO</sub>	Emitter to Collector	I <sub>E</sub> = 100μA, I <sub>F</sub> = 0	All	7	10		
I <sub>CEO</sub>	Leakage Current Collector to Emitter	V <sub>CE</sub> = 10 V, I <sub>F</sub> = 0	All		1	50	nA
I <sub>CBO</sub>	Collector to Base	V <sub>CB</sub> = 10 V, I <sub>F</sub> = 0	CNY171M/2M/3M/4M			20	nA
C <sub>CE</sub>	Capacitance Collector to Emitter	V <sub>CE</sub> = 0, f = 1MHz	All		8		pF
C <sub>CB</sub>	Collector to Base	V <sub>CB</sub> = 0, f = 1MHz	CNY171M/2M/3M/4M		20		pF
C <sub>EB</sub>	Emitter to Base	V <sub>EB</sub> = 0, f = 1MHz	CNY171M/2M/3M/4M		10		pF

### Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.*	Max.	Units
V <sub>ISO</sub>	Input-Output Isolation Voltage	f = 60 Hz, t = 1 sec., I <sub>I-O</sub> ≤ 2μA <sup>(4)</sup>	7500			Vac(pk)
R <sub>ISO</sub>	Isolation Resistance	V <sub>I-O</sub> = 500 VDC <sup>(4)</sup>	10 <sup>11</sup>			Ω
C <sub>ISO</sub>	Isolation Capacitance	V <sub>I-O</sub> = ∅, f = 1MHz <sup>(4)</sup>		0.2		pF

### Transfer Characteristics (T<sub>A</sub> = 25°C Unless otherwise specified.)<sup>(3)</sup>

Symbol	DC Characteristics	Test Conditions	Min.	Typ.*	Max.	Units	
<b>COUPLED</b>							
(CTR) <sup>(2)</sup>	Output Collector Current	MOC8106M	I <sub>F</sub> = 10mA, V <sub>CE</sub> = 10V		50	150	%
		MOC8107M			100		
		CNY17F1M	I <sub>F</sub> = 10mA, V <sub>CE</sub> = 5V		40	80	
		CNY17F2M			63	125	
		CNY17F3M			100	200	
		CNY17F4M			160	320	
		CNY171M			40	80	
		CNY172M			63	125	
		CNY173M			100	200	
		CNY174M			160	320	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	CNY17XM/FXM	I <sub>C</sub> = 2.5mA, I <sub>F</sub> = 10mA			0.4	V
		MOC8106M/7M	I <sub>C</sub> = 500μA, I <sub>F</sub> = 5.0mA				

\*All typicals at T<sub>A</sub> = 25°C

**Electrical Characteristics** (Continued) ( $T_A = 25^\circ\text{C}$  Unless otherwise specified.)<sup>(1)</sup>

**Transfer Characteristics** (Continued)<sup>(3)</sup>

Symbol	AC Characteristics <sup>(4)</sup>		Test Conditions	Min.	Typ.*	Max.	Units
<b>NON-SATURATED SWITCHING TIME</b>							
$t_{on}$	Turn-On Time	All Devices	$I_C = 2.0\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$		2	10	$\mu\text{s}$
$t_{off}$	Turn-Off Time	All Devices	$I_C = 2.0\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$		3	10	$\mu\text{s}$
$t_d$	Delay Time	CNY17XM/XFM	$I_F = 10\text{mA}, V_{CC} = 5\text{V}, R_L = 75\Omega$			5.6	$\mu\text{s}$
$t_r$	Rise Time	All Devices	$I_C = 2.0\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$		1		$\mu\text{s}$
		CNY17XM/FXM	$I_F = 10\text{mA}, V_{CC} = 5\text{V}, R_L = 75\Omega$			4.0	
$t_s$	Storage Time	CNY17XM/FXM	$I_F = 10\text{mA}, V_{CC} = 5\text{V}, R_L = 75\Omega$			4.1	$\mu\text{s}$
$t_f$	Fall Time	All Devices	$I_C = 2.0\text{mA}, V_{CC} = 10\text{V}, R_L = 100\Omega$		2		$\mu\text{s}$
		CNY17XM/FXM	$I_F = 10\text{mA}, V_{CC} = 5\text{V}, R_L = 75\Omega$			3.5	
<b>SATURATED SWITCHING TIMES</b>							
$t_{on}$	Turn-on Time	CNY171M/F1M	$I_F = 20\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			5.5	$\mu\text{s}$
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			8.0	
$t_r$	Rise Time	CNY171M/F1M	$I_F = 20\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			4.0	$\mu\text{s}$
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			6.0	
$t_d$	Delay Time	CNY171M/F1M	$I_F = 20\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			5.5	$\mu\text{s}$
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			8.0	
$t_{off}$	Turn-off Time	CNY171M/F1M	$I_F = 20\text{mA}, V_{CE} = 0.4\text{V}$			34	$\mu\text{s}$
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10\text{mA}, V_{CE} = 0.4\text{V}$			39	
$t_f$	Fall Time	CNY171M/F1M	$I_F = 20\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			20.0	$\mu\text{s}$
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			24.0	
$t_s$	Storage Time	CNY171M/F1M	$I_F = 20\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			34.0	$\mu\text{s}$
		CNY172M/3M/4M CNY17F2M/F3M/F4M	$I_F = 10\text{mA}, V_{CC} = 5\text{V}, R_L = 1\text{k}\Omega$			39.0	

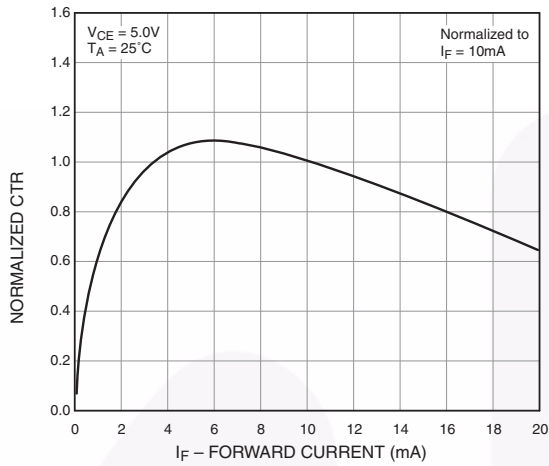
\*All typicals at  $T_A = 25^\circ\text{C}$

**Notes:**

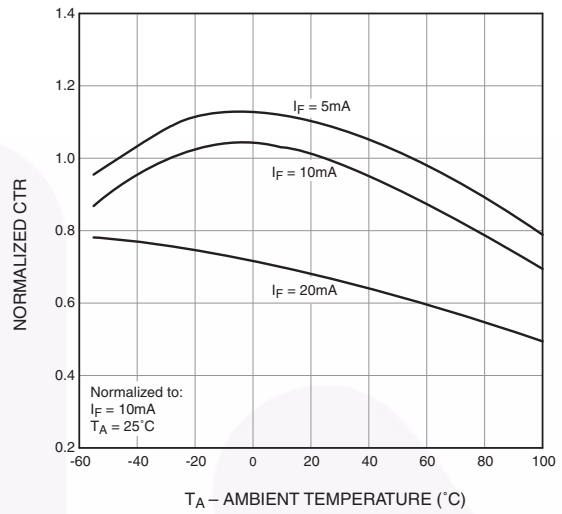
1. Always design to the specified minimum/maximum electrical limits (where applicable).
2. Current Transfer Ratio (CTR) =  $I_C/I_F \times 100\%$ .
3. For test circuit setup and waveforms, refer to Figures 10 and 11.
4. For this test, Pins 1 and 2 are common, and Pins 4 and 5 are common.

## Typical Performance Characteristics

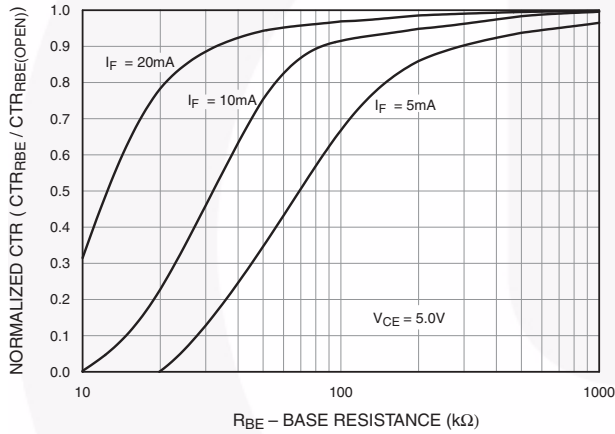
**Fig. 1 Normalized CTR vs. Forward Current**



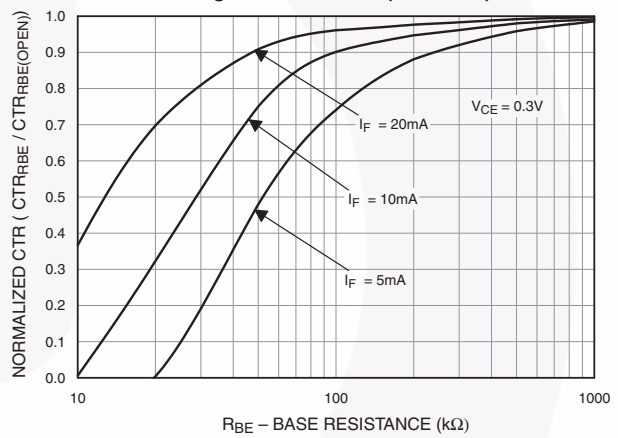
**Fig. 2 Normalized CTR vs. Ambient Temperature**



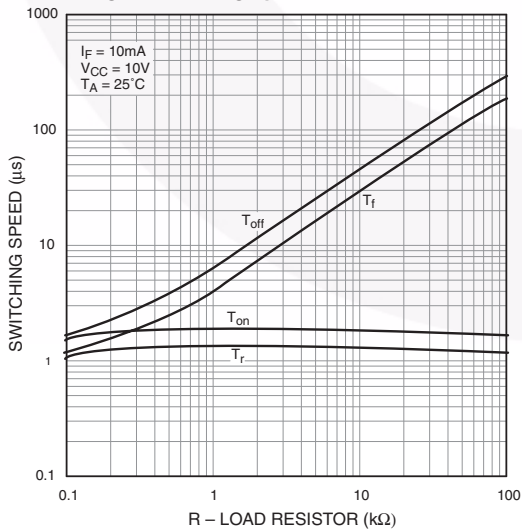
**Fig. 3 CTR vs. RBE (Unsaturated)**



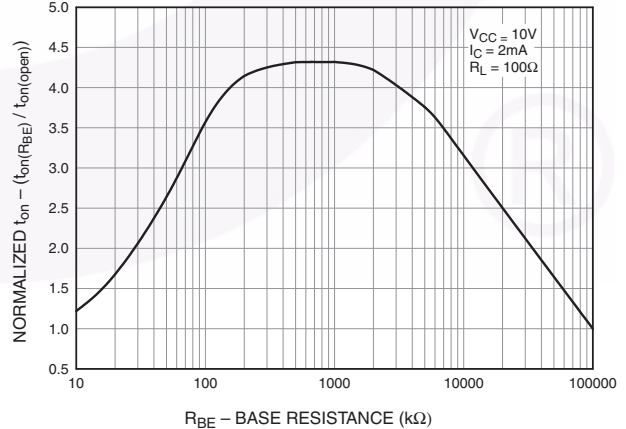
**Fig. 4 CTR vs. RBE (Saturated)**



**Fig. 5 Switching Speed vs. Load Resistor**



**Fig. 6 Normalized ton vs. RBE**



Typical Performance Characteristics (Continued)

Fig. 7 Normalized  $t_{off}$  vs.  $R_{BE}$

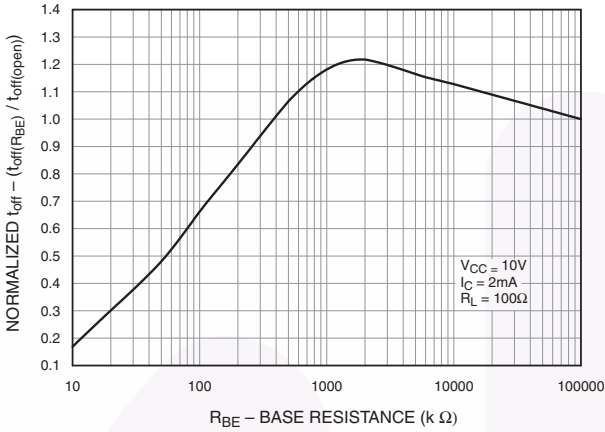


Fig. 8 LED Forward Voltage vs. Forward Current

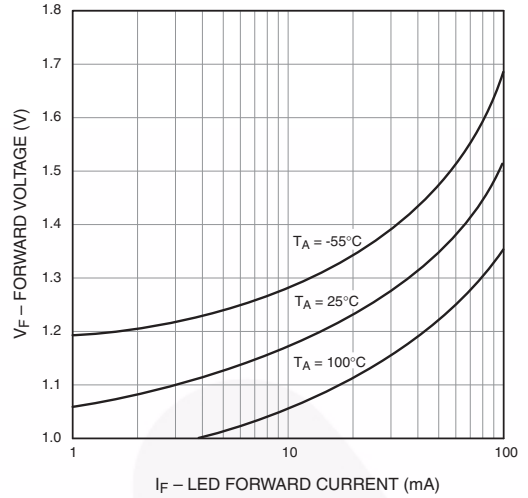


Fig. 9 Collector-Emitter Saturation Voltage vs Collector Current

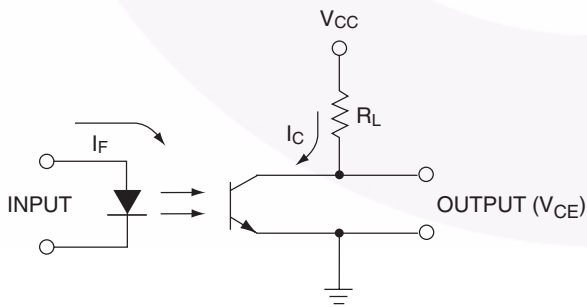
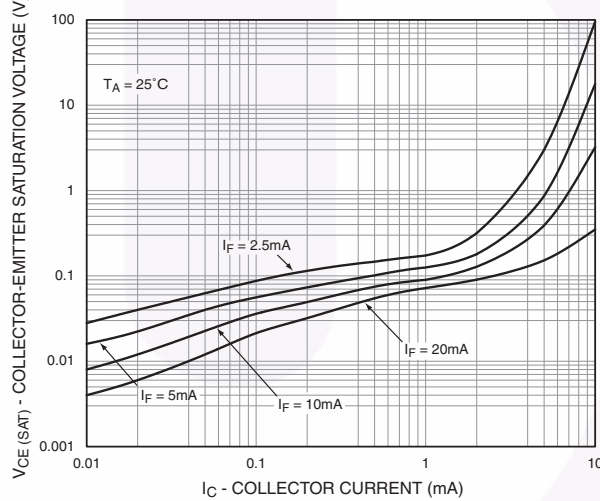


Figure 10. Switching Time Test Circuit

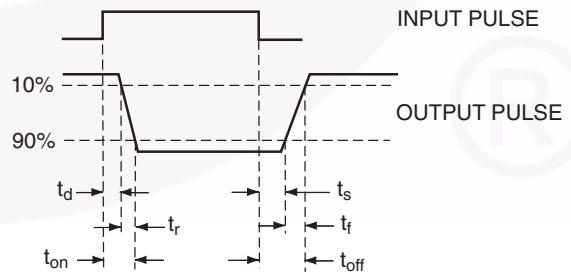
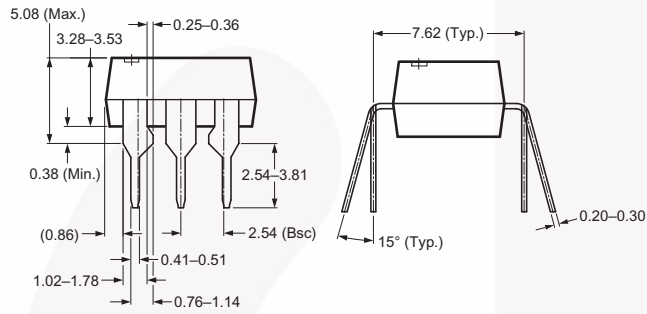


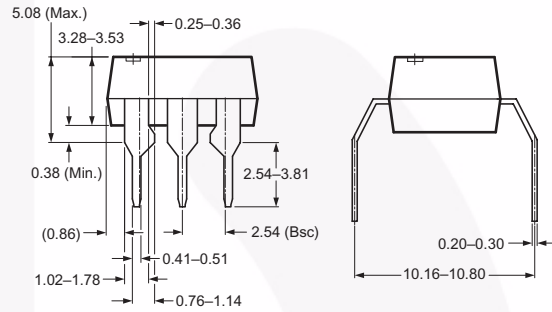
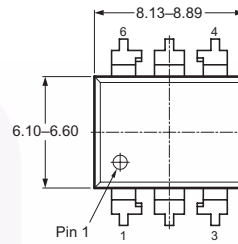
Figure 11. Switching Time Waveforms

## Package Dimensions

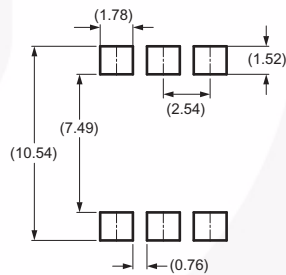
### Through Hole



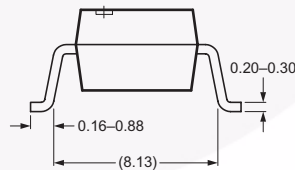
### 0.4" Lead Spacing



### Surface Mount



Recommended Pad Layout

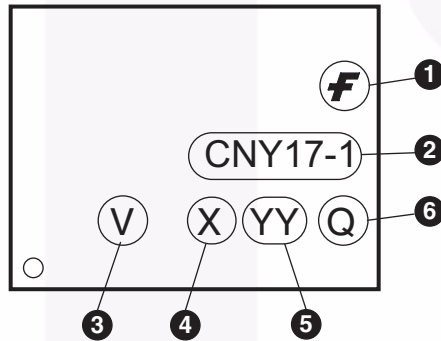


**Note:**  
All dimensions in mm.

### Ordering Information

Option	Order Entry Identifier (Example)	Description
No option	CNY171M	Standard Through Hole Device
S	CNY171SM	Surface Mount Lead Bend
SR2	CNY171SR2M	Surface Mount; Tape and Reel
T	CNY171TM	0.4" Lead Spacing
V	CNY171VM	IEC60747-5-2
TV	CNY171TVM	IEC60747-5-2, 0.4" Lead Spacing
SV	CNY171SVM	IEC60747-5-2, Surface Mount
SR2V	CNY171SR2VM	IEC60747-5-2, Surface Mount, Tape and Reel

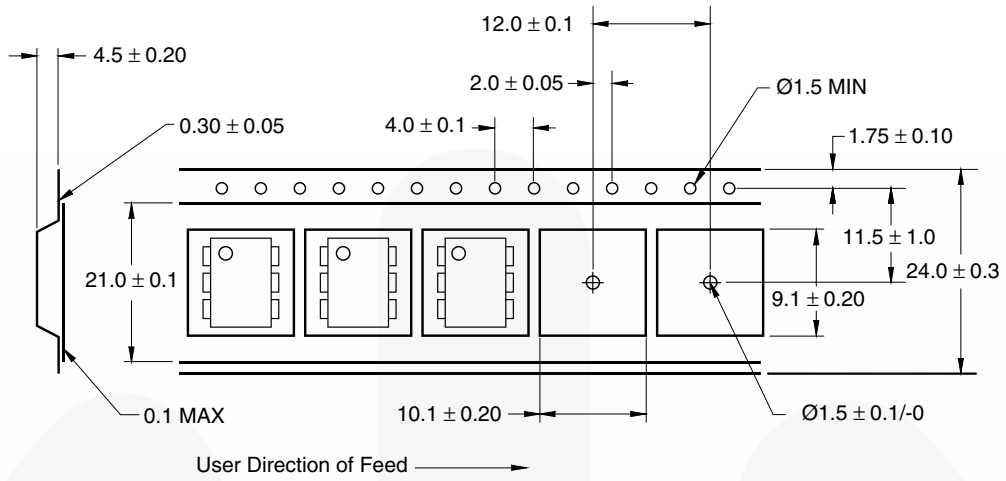
### Marking Information



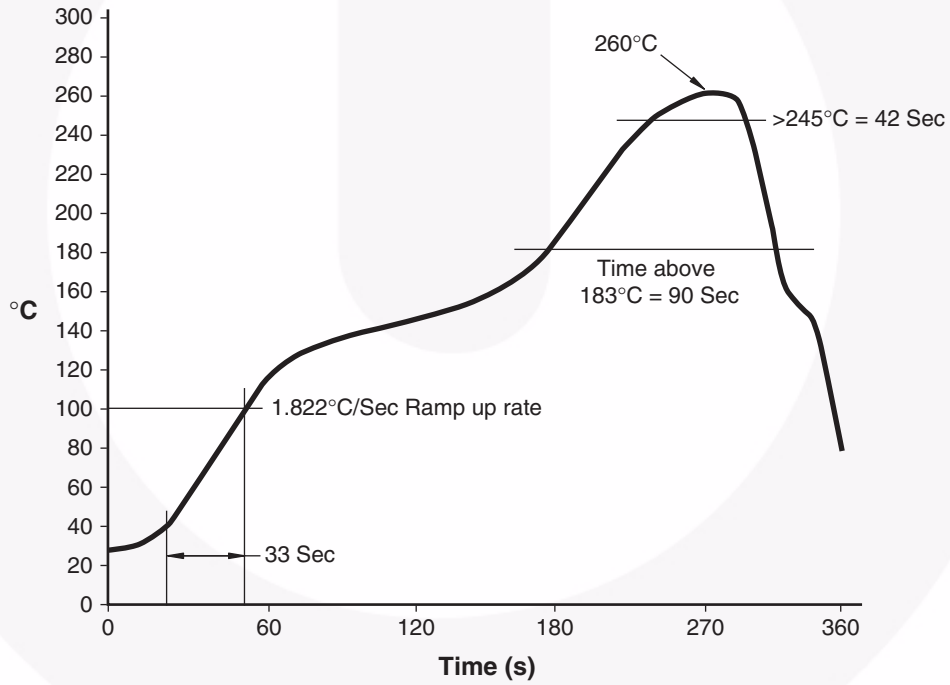
Definitions	
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '7'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code



### Carrier Tape Specification






### Reflow Profile





**TRADEMARKS**

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

- |  |   |  |   |
|--|---|--|---|
| Auto-SPM™  | F-PFS™  | PowerTrench®   | The Power Franchise®  |
| Build it Now™  | FRFET®  | PowerXS™   | the power franchise   |
| CorePLUS™  | Global Power Resource SM  | Programmable Active Droop™   | TinyBoost™  |
| CorePOWER™   | Green FPS™  | QFET®  | TinyBuck™   |
| CROSSVOLT™   | Green FPS™ e-Series™  | QS™  | TinyLogic®  |
| CTL™   | Gmax™   | Quiet Series™  | TINYOPTO™   |
| Current Transfer Logic™  | GTO™  | RapidConfigure™  | TinyPower™  |
| EcoSPARK®  | IntelliMAX™   |  ™  | TinyPWM™  |
| EfficientMax™  | ISOPLANAR™  | Saving our world, 1mW/W/kW at a time™  | TinyWire™   |
| EZSWITCH™*   | MegaBuck™   | SmartMax™  | TriFault Detect™  |
|  ™* | MICROCOUPLER™   | SMART START™   | TRUECURRENT™*   |
|  ®  | MicroFET™   | SPM®   | µSerDes™  |
| Fairchild®   | MicroPak™   | STEALTH™   |  ™ |
| Fairchild Semiconductor®   | MillerDrive™  | SuperFET™  | UHC®  |
| FACT Quiet Series™   | MotionMax™  | SuperSOT™-3  | Ultra FRFET™  |
| FACT®  | Motion-SPM™   | SuperSOT™-6  | UniFET™   |
| FAST®  | OPTOLOGIC®  | SuperSOT™-8  | VCX™  |
| FastvCore™   | OPTOPLANAR®   | SupreMOS™  | VisualMax™  |
| FETBench™  |  ™ | SyncFET™   | XS™   |
| FlashWriter®*  | PDP SPM™  | Sync-Lock™   |   |
| FPS™   | Power-SPM™  |  ®* |   |

\* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

**DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

**LIFE SUPPORT POLICY**

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

**ANTI-COUNTERFEITING POLICY**

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, [www.fairchildsemi.com](http://www.fairchildsemi.com), under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

**PRODUCT STATUS DEFINITIONS**

**Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I40